

Docket No.: 61352-041

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Hiroyuki FURUYA, et al.

Serial No.: Continuation of Application No. :

PCT/JP02/13350

: Group Art Unit:

Filed: July 17, 2003

: Examiner:

For: METHOD OF FABRICATING NITRIDE BASED SEMICONDUCTOR SUBSTRATE
AND METHOD OF FABRICATING NITRIDE BASED SEMICONDUCTOR DEVICE

PRELIMINARY AMENDMENT

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Sir:

Prior to examination of the above-referenced application, please amend the application as

follows: